MOSFETs Silicon N-Channel MOS (DTMOSIV-H)

# TK25N60X5

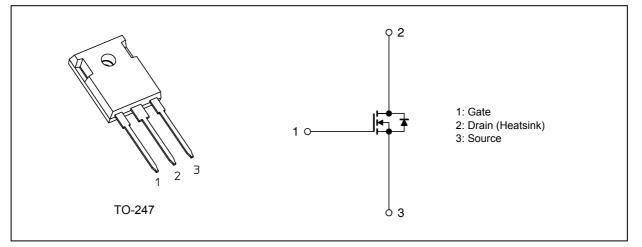
#### 1. Applications

• Switching Voltage Regulators

#### 2. Features

- (1) Fast reverse recovery time:  $t_{rr} = 120 \text{ ns}(typ.)$
- (2) Low drain-source on-resistance:  $R_{DS(ON)} = 0.12 \Omega(typ.)$
- (3) Easy to control Gate switching
- (4) Enhancement mode:  $V_{th}$  = 3 to 4.5 V( $V_{DS}$  = 10 V,  $I_D$  = 1.2 mA)

### 3. Packaging and Internal Circuit



### 4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

Characteristics			Rating	Unit
Drain-source voltage		V <sub>DSS</sub>	600	V
Gate-source voltage		V <sub>GSS</sub>	±30	
Drain current (DC)	(Note 1)	I <sub>D</sub>	25	Α
Drain current (pulsed)	(Note 1)	I <sub>DP</sub>	100	
Power dissipation	(T <sub>c</sub> = 25 °C)	PD	180	W
Single-pulse avalanche energy	(Note 2)	E <sub>AS</sub>	305	mJ
Avalanche current		I <sub>AR</sub>	6.2	A
Reverse drain current (DC)	(Note 1)	I <sub>DR</sub>	25	
Reverse drain current (pulsed)	(Note 1)	I <sub>DRP</sub>	100	
Channel temperature		T <sub>ch</sub>	150	°C
Storage temperature		T <sub>stg</sub>	-55 to 150	7
Mounting torque		TOR	0.8	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production

2014-09

#### 5. Thermal Characteristics

Characteristics		Max	Unit
Channel-to-case thermal resistance	R <sub>th(ch-c)</sub>	0.694	°C/W
Channel-to-ambient thermal resistance	R <sub>th(ch-a)</sub>	50	

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: V<sub>DD</sub> = 90 V, T<sub>ch</sub> = 25 °C (initial), L = 13.9 mH, R<sub>G</sub> = 25  $\Omega$ , I<sub>AR</sub> = 6.2 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

#### 6. Electrical Characteristics

### 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±30 V, $V_{DS}$ = 0 V	_	_	±1	μA
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V	_	_	100	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	600	_	—	V
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.2 mA	3	_	4.5	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 7.5 A		0.12	0.14	Ω

### 6.2. Dynamic Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	$V_{DS}$ = 300 V, $V_{GS}$ = 0 V, f = 100 kHz	_	2400	_	pF
Reverse transfer capacitance	C <sub>rss</sub>		_	6	_	
Output capacitance	C <sub>oss</sub>		_	60	_	
Effective output capacitance	C <sub>o(er)</sub>	$V_{DS}$ = 0 to 400 V, $V_{GS}$ = 0 V		100	_	
Gate resistance	r <sub>g</sub>	V <sub>DS</sub> = OPEN , f = 1 MHz	_	1.7	_	Ω
Switching time (rise time)	t <sub>r</sub>	See Figure 6.2.1	_	40	_	ns
Switching time (turn-on time)	t <sub>on</sub>		_	80	_	
Switching time (fall time)	t <sub>f</sub>		_	4	_	
Switching time (turn-off time)	t <sub>off</sub>		_	100	_	
MOSFET dv/dt ruggedness	dv/dt	V <sub>DD</sub> = 0 to 400 V, I <sub>D</sub> = 12.5 A	50	_	_	V/ns

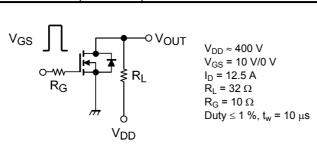


Fig. 6.2.1 Switching Time Test Circuit

### 6.3. Gate Charge Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, \text{ V}_{GS}$ = 10 V, I <sub>D</sub> = 25 A		60	_	nC
Gate-source charge 1	Q <sub>gs1</sub>		_	20	_	
Gate-drain charge	Q <sub>gd</sub>			30	_	

### 6.4. Source-Drain Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V <sub>DSF</sub>	I <sub>DR</sub> = 25 A, V <sub>GS</sub> = 0 V	_	_	-1.7	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 12.5 A, V <sub>GS</sub> = 0 V	_	120	192	ns
Reverse recovery charge	Q <sub>rr</sub>	-dI <sub>DR</sub> /dt = 100 A/µs	_	0.6	_	μC
Peak reverse recovery current	I <sub>rr</sub>		_	10	_	А
Diode dv/dt ruggedness	dv/dt	$I_{DR}$ = 12.5 A, $V_{GS}$ = 0 V, $V_{DD}$ = 400 V	50			V/ns

### 7. Marking (Note)

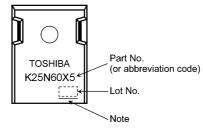


Fig. 7.1 Marking

 Note:
 A line under a Lot No. identifies the indication of product Labels.

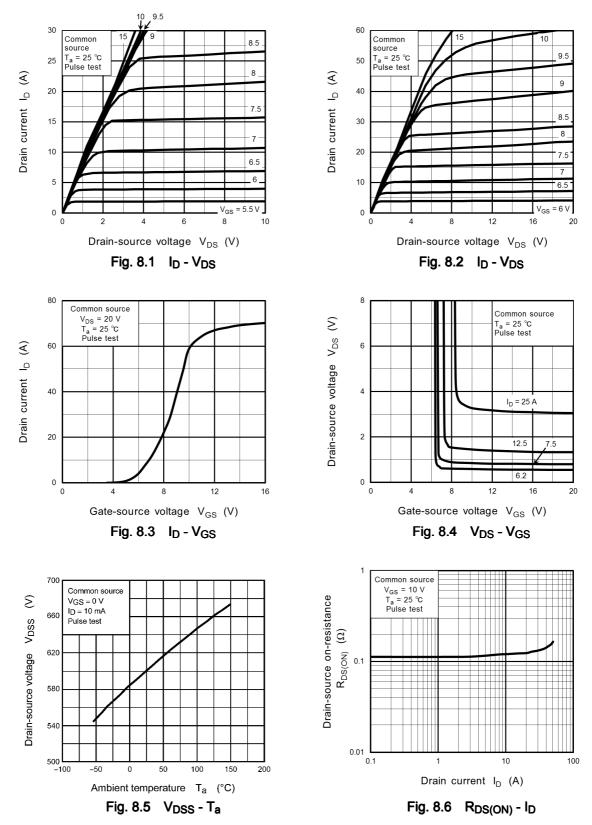
 Not underlined:
 [[Pb]]/INCLUDES > MCV

 Underlined:
 [[G]]/RoHS COMPATIBLE or
 [[G]]/RoHS [[Pb]]

 Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

 The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

### 8. Characteristics Curves (Note)



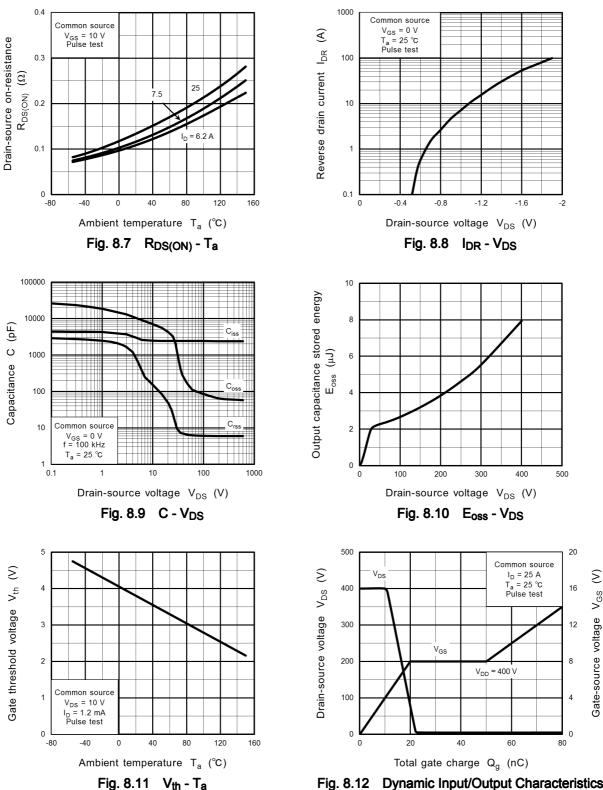
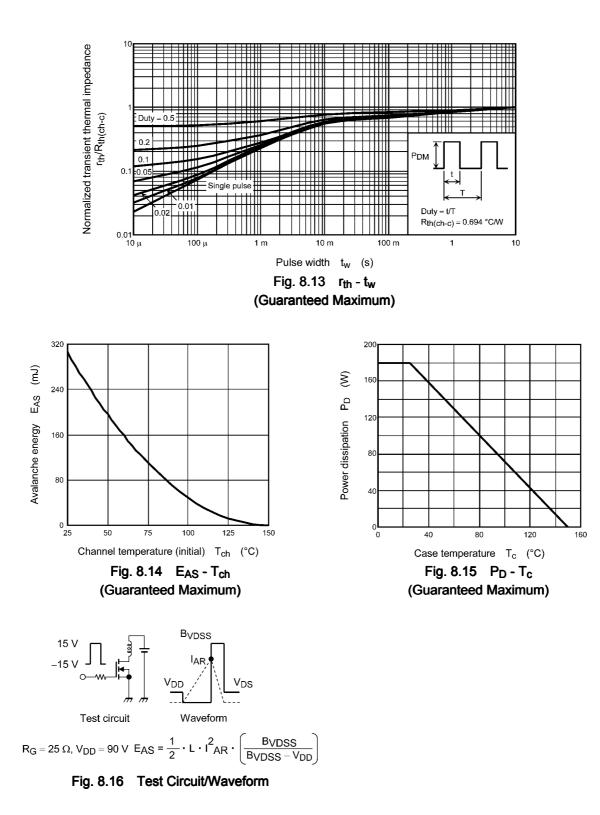
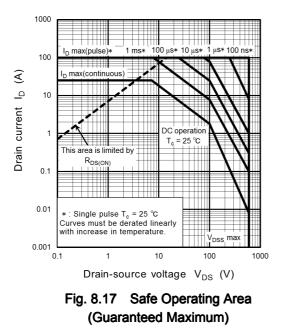


Fig. 8.12 Dynamic Input/Output Characteristics

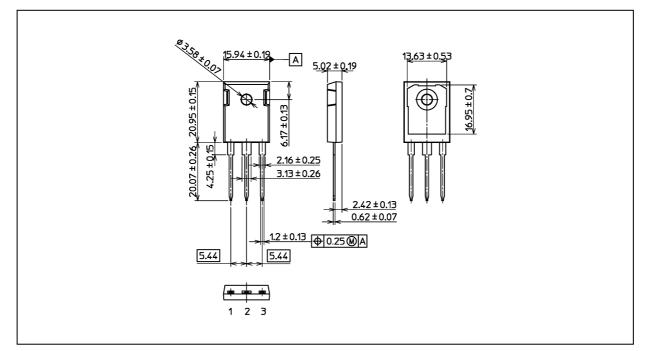




Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

### Package Dimensions

Unit: mm



#### Weight: 6.15 g (typ.)

Package Name(s)	
JEITA: SC-65	
TOSHIBA: 2-16L1A	
Nickname: TO-247	

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